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Table of Contents

Session 1: Applications

- 1.1 Power switch improvement for RO array characterization in 18nm FD-SOI technology platform validation 3
C. Cagli, F. Pourchon, H. Degoirat, J. B. Moulard, F. Granoux, M. Dahmani, R. Wilson
STMicroelectronics, 850 Rue Jean Monnet, Crolles, France
- 1.2 Comparative Study of Switching Dynamics in Ferroelectric-based Capacitors with Different Design Options 7
Francesco Driussi, Enrico Rocco, Marco Massarotto, Suzanne Lancaster¹
DPIA, Università degli Studi di Udine, Italy
¹*NaMLab gGmbH, Dresden, Germany*
²*Chair of Nanoelectronics, IHM, TU–Dresden, Germany*
- 1.3 Enhancement of Synaptic Properties using Ta₂O₅/ZnO/Ta₂O₅ Tri-layer Device 12
Chae-Min Yeom, Sung-Ho Kim, Yu-Bin Kim, Dong-Min Kim, Kil-Sun Roh¹, Young-Su Kim¹, Yong-Goo Kim², Hyuk-Min Kwon³, Hi- Deok Lee
Department of Electronics Engineering, Chungnam National University, Daejeon, Korea
¹*LAB of Nano Process Technology, National Nanofab Center, Daejeon, Korea*
²*Department of Green Semiconductor System, Korea Polytechnic, Daegu, Korea*
³*School of Electronic & Electrical Engineering, Hankyong National University, Anseong, Korea*

Session 2: Reliability

- 2.1 The Hot Carrier Injection Induced Degradation in MOS Transistors with Subthreshold Hump and the Corelated Impacts on Low Frequence Noise for Low Power Analog Designs 19
Wuxia Li, Kejun Xia¹, Rayne Xu², Lie Chao²
NXP Semiconductors, Tianjin AIoT Lab
¹*TSMC, Power Management Business Development*
²*NXP Semiconductors, Front End Innovation*

- 2.2 On-Wafer Characterization of HCI/BTI-induced Threshold Voltage Degradation based Measured Frequency Shift of Ring-Oscillator Circuits 24
Chika Tanaka, Nobuyuki Momo, Fumie Fujii, Osamu Kobayashi
Memory Division, Kioxia Corporation, Yokohama, Japan
- 2.3 SiC DMOSFET Real Wafer Level HTRB and HTGB Evaluation 29
Ng Hong Seng, Tan Ai Heong¹, Beh Shun Xiar¹, Lee Johnny², Lin Jai Wei¹
X-FAB Sarawak, Kuching, Malaysia
¹*Nexustest, Singapore*
²*X-FAB Texas, Lubbock, TX, USA*
- 2.4 Novel Fractal Points Implementation for Electron Beam Inspection (EBI) and Data Analysis 33
Po Jen Mo, Tsan Yu Ho¹, Tomoya Asano¹, Xing Ji²
Micron Technology, Taichung City, Taiwan, R.O.C.
¹*Micron Technology, Higashi Hiroshima-shi, Japan*
²*Micron Technology, Singapore, Singapore*
- 2.5 Withdrawn

Session 3: Device Characterization

- 3.1 Withdrawn
- 3.2 D-Mode GaN/AlGaIn/GaN MOS-HEMT Test Structures for Evaluating Gate Dielectric Impact on Device Performance 43
Andres S. Aguirre-Sanchez, Rajni Aggarwal, Chadwin D. Young, Rodolfo A. Rodriguez-Davila, Jonathan Anderson¹, Edwin L. Piner¹, Manuel A. Quevedo
Materials Science & Engineering, University of Texas at Dallas, Richardson, TX, USA
¹*Materials Application Research Center Texas State University, San Marcos, TX, USA*
- 3.3 TACHI: Tests as a Chip Identifier 47
Ryosuke Sada, Ryo Shirai, Michihiro Shintani¹, Takashi Sato
Kyoto University, Kyoto, Japan
¹*Kyoto Institute of Technology, Kyoto, Japan*
- 3.4 Reducing Short-Circuit current of CMOS Inverter circuits with “PN-Body Tied SOI-FET” 53
Kazuki Nakahashi, Takayuki Mori, Jiro Ida
Kanazawa Institute of Technology, Nonoichi, Japan

Session 4: Design & Layout

- 4.1 Layout experiments and test structures to characterize Local Layout Effects due to mechanical stress in FinFET transistors 59
Angelo Rossoni, Tomasz Brozek¹, Sharad Saxena², Rajesh Khamankar², Christopher Hess¹, Jurcy Huang³, Yuchen Teng³, Zsolt Kovacs-Vajna⁴, Michele Quarantelli
PDF Solutions, Inc., Brescia, Italy
¹*PDF Solutions, Inc., Santa Clara, CA, USA*
²*PDF Solutions, Inc., Dallas, TX, USA*
³*PDF Solutions, Inc., Hsinchu, Taiwan*
⁴*Dept. of Information Engineering, University of Brescia, Brescia, Italy*
- 4.2 Estimating Verticality Parameters in Deep Reactive Ion Etching using MEMS Oscillators 63
Shun Yasunaga, Yoshio Mita
The University of Tokyo, Tokyo, Japan
- 4.3 Non-uniformities in MOSFET-array characteristics caused by probe-induced mechanical stress 68
Pablo Sarazá-Canflanca, Xue Fan¹, Simon Van Beek, Erik Bury, Ben Kaczer
imec, Leuven, Belgium
¹*Chengdu Technological University, Sichuan, China*
- 4.4 Methodology and Test Structures for Studying β -Ga₂O₃ Dielectric and Contact Interfaces 74
A. A. Gruszecki, J. Roy, K. S. Agrawal¹, P. La Torraca¹, K. Cherkaoui¹, P. K. Hurley¹, R. M. Wallace, C. D. Young
Department of Materials Science and Engineering, The University of Texas at Dallas, Richardson, TX, USA
¹*Tyndall National Institute, University College Cork, Cork, Ireland*

Session 5: RF & Power

- 5.1 A new test structure for charge pumping current measurement in vertical Si power device 83
Tatsuya Ohguro, Kohei Oasa, Takuya Yasutake, Takuma Hara, Tatsuya Nishiwaki, Kenya Kobayashi, Hiroaki Kato
Advanced Semiconductor Device Development Center, Toshiba Electronic Devices & Storage Corporation
- 5.2 A Novel Separated Source Electrodes Kelvin (SSEK) Structure for Extracting Channel Mobility in the 4H-SiC VDMOSFET 87
Wen-Shu Chen, An-Ching Li, Chia-Lung Hung¹, Yi-Kai Hsiao¹, Bing-Yue Tsui
Institute of Electronics, National Yang Ming Chiao Tung University, Hsinchu, Taiwan, R.O.C.
¹*Semiconductor Research Center, Hon Hai Research Institute, Hsinchu, Taiwan, R.O.C.*
- 5.3 Modified Angelov Model with Improved Accuracy for RF GaN-on-Si HEMTs 91
David C. Chen, Min Li Chou, Kerwin Lin, Mike Hsieh, Perry Lin, Heng Ching Lin, Kevin Lee, Alex Hou, Barry Lin, M. C. Lai
Wavetek Microelectronics Corporation (WTK), HsinChu, Taiwan
- 5.4 Passive and Causal Modeling of 300-GHz-Band IC Capacitors Using Rational Polynomial Approximation 95
Shun Beppu, Yuto Hirayama, Shinsuke Hara¹, Akifumi Kasamatsu¹, Yoshio Mita², Kyoya Tkano
Department of Electrical Engineering, Tokyo University of Science, Chiba, Japan
¹*National Institute of Information and Communications Technology, Tokyo, Japan*
²*Department of Electrical Engineering, Tokyo University of Science, Tokyo, Japan*

Session 6: Cryogenic Measurements

- 6.1 Oscillation in Cryogenic DC Measurements of High Power LDMOS Devices and Solution 101
Yili Wang, Kejun Xia¹, Guofu Niu, Michael Hamilton, Xu Cheng²
Alabama Micro/Nanoelectronics Science and Technology Center, Auburn University, Auburn, AL, USA
¹*TSMC, Taiwan, R.O.C.*
²*NXP Semiconductors, Arizona, USA*

- 6.2 Measurement of Subthreshold Current Variability at 1.5 K Using Addressable MOSFET Array 106
 Tomoko Mizutani, Kiyoshi Takeuchi, Takuya Saraya, Hiroshi Oka¹, Takahiro Mori¹,
 Masaharu Kobayashi², Toshiro Hiramoro
Institute of Industrial Science, The University of Tokyo, Tokyo, Japan
¹*National Institute of Advanced Industrial Science and Technology (AIST), Ibaraki, Japan*
²*Systems Design Lab (d.lab), The University of Tokyo, Tokyo, Japan*
- 6.3 Hysteresis-Induced Neuromorphic Behavior in 180nm Bulk PMOS Devices at 3K 111
 Fiheon Imroze, Bhavani Yalagala, Meraj Ahmad, Mostafa Elsayed, Robert Graham,
 Giuseppe Colletta, Hadi Heidari, Martin Weides
James Watt School of Engineering, University of Glasgow, Glasgow, United Kingdom

Session 7: Process Characterization

- 7.1 A Test Structure for Analyzing Self-Heating Induced Distortion in On-Chip Current Sensing Resistors 119
 Heng Ma, Shoubhik Karmakar, Huajun Zhang, Yuyan Liu, Haidong Guo¹, Marco Berkhout², Qinwen Fan
Delft University of Technology, Delft, The Netherlands
¹*ams OSRAM, Plano, TX, USA*
²*Monolithic Power Systems, Enschede, The Netherlands*
- 7.2 Novel Test Structures for 3D NAND Array Plasma Damage Monitoring 124
 Keerti Kalia, Roberta Rita Bottini¹, Ken Marr, Allen Mcteer, Cheah Zhin Mow², James Davis
Micron Technology, Inc., Boise, ID, USA
¹*Micron Technology, Inc., Vimercate, Italy*
²*Micron Technology, Inc., Singapore*

- 7.3 Advantage and Challenge of Electrical Critical Dimension Test Structures for Electroplated High Aspect Ratio Nano Structures (HARNS) on Insulating Materials 129
 Yoshio Mita, Ayako Mizushima, Noriko Kawai¹, Tsuboi Shinji¹, Yurie Inoue¹, Etsuko Ohta¹, Shun Yasunaga, Ryosho Nakane¹, David Bourrier², Amel Beghersa², Hugues Granier², Akio Higo¹
Department of Electrical Engineering and Information Systems, the University of Tokyo, Tokyo, Japan
¹*Systems Design Lab (d.lab), School of Engineering, the University of Tokyo, Tokyo, Japan*
²*LAAS-CNRS, Toulouse, France*
- 7.4 Fabrication of NbO₂ based IMT Selector Devices via 300nm Based Memory Test Vehicle 133
 Karsten Beckmann, Martin Rodgers, Theodore Wallach¹, Ross Paries¹, Nathaniel Cady¹
NY CREATES, Albany, NY, USA
¹*College of Nanotechnology, Science, and Engineering, University at Albany, Albany, NY, USA*

Session 8: Test Optimization

- 8.1 Smart Diagnostics for 3D CFET: A Machine Learning Approach to Failure Analysis 143
 Jerome Mitard, Husnu Murat Kocak¹, Thomas Chiarella, Cassie Sheng², Steven Demuyck², Naoto Horiguchi²
Compute Technology Device Department, IMEC, Belgium
¹*Imec & Department of Computer Science, KU Leuven, Belgium*
²*Process Integration Department, IMEC, Belgium*
- 8.2 Automatic PSP MOSFET model card extraction powered by deep learning 147
 Alba Ordonez Rodriguez, Fabien Gilibert, Francois Paolini, Alan Gerard;Elouan Vincent, Nicolas Derrier, Matthieu Quoirin, Pascal Urard, John Samuel, Remy Cellier¹, Lioua Labrak¹, Nacer Abouchi
STMicroelectronics, Crolles, France
¹*CPE Lyon - LIRIS CNRS UMR 5205, University of Lyon, Lyon, France*
- 8.3 Active Sampling of Electrical Characterization Parameters for Efficient Measurement 151
 Husnu Murat Kocak, Jerome Mitard¹, Ahmet Teoman Naskali², Jesse Davis
Department of Computer Science, KU Leuven, Belgium
¹*Compute Technology Device Department, IMEC, Belgium*
²*Department of Computer Engineering, Galatasaray University, Turkey*

- 8.4 Test Accuracy Improvement of Ensemble Gaussian Process-based IC Outlier Detection 157
Using Temporal Similarity among Wafers
Daisuke Goeda, Tomoki Nakamura¹, Masuo Kajiyama¹, Makoto Eiki¹, Hajime Takayama, Takashi Sato², Michihiro Shintani
Graduate School of Science and Technology, Kyoto Institute of Technology, Kyoto, Japan
¹*Sony Semiconductor Manufacturing Corporation, Isahaya-shi, Japan*
²*Graduate School of Informatics, Kyoto University, Kyoto, Japan*
- 8.5 Evaluation of Rapid Vt testing of Wafer-Level MOSFETs. 163
Michael H. Herman, Ben Morris
Parametric Test Group, Advantest America, San Jose, CA, USA

Session 9: MEMS & Sensors

- 9.1 Microheater integration in gate dielectric functionalized IGZO thin film transistors for 173
methanol sensing
M. Calderon-Gonzalez, M.L. Tietze¹, S. Mondal, E. Georgitzikis, D. Cheyns¹, R. Ameloot², J. Genoe
imec, Leuven, Belgium
¹*Department of Microbial and Molecular Systems (M2S), KU Leuven, Belgium*
²*Department of Electrical Engineering (ESAT) KU Leuven, Belgium*
- 9.2 Enhanced Permittivity in PEALD Al₂O₃/TiO₂ Nanolaminates: Investigating Maxwell- 179
Wagner and Interfacial Polarization in IDEs
Z. Mousavi Karimi, J. A. Davis
Department of Electrical and Computer Engineering, Georgia Institute of Technology, Atlanta, GA, USA
- 9.3 Planar FDSOI Reconfigurable Schottky Barrier FETs for Gas Sensing 183
Andreas Kramer, Tillmann Krauss, Maximilian Reuter, Julian Kulenkampff, Dominic Korner, Klaus Hofmann
Integrated Electronic Systems Lab, Technical University of Darmstadt, Darmstadt, Germany

- Author Index 188